

Ballistic G/hBN heterostructures: focusing and caustics in graphene devices

Vladimir Falko



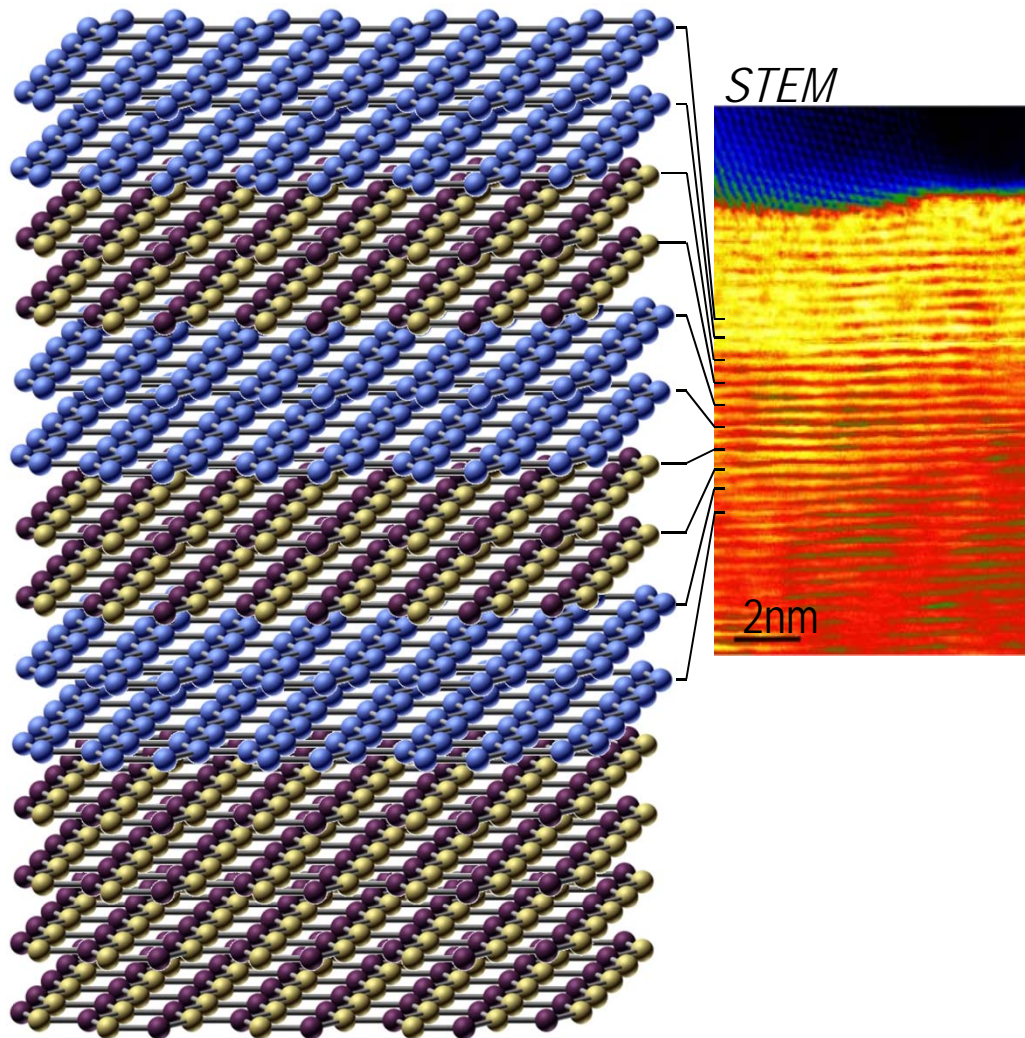
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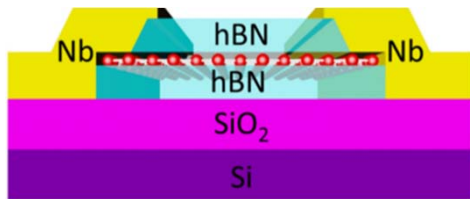


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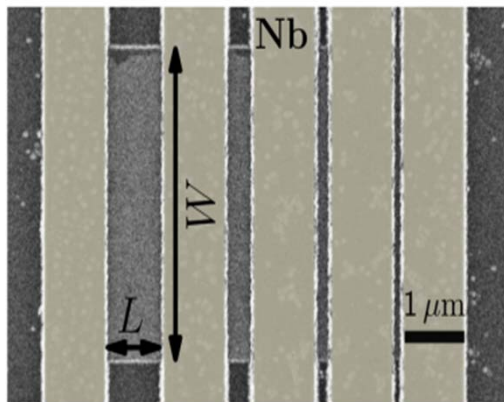
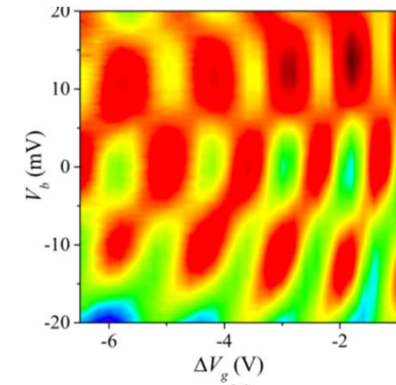
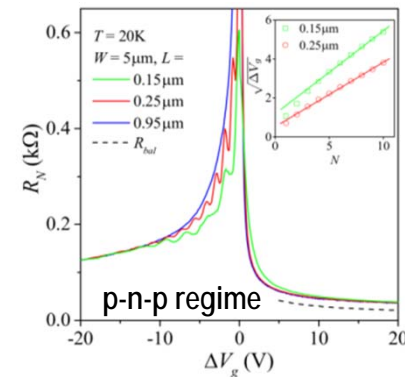


- Ballistic effects in G/hBN
- Electron focusing at p-n junction in graphene
- Caustics of snake orbits near p-n junction in graphene in magnetic field
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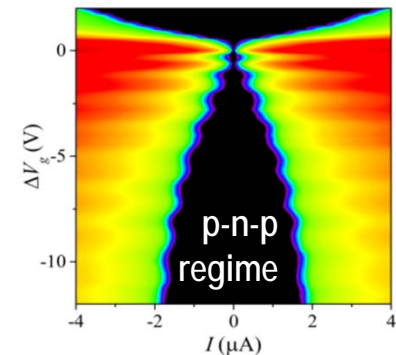
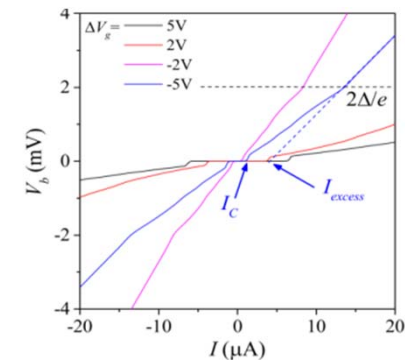
hBN-encapsulated graphene: sample-length ballistic transport



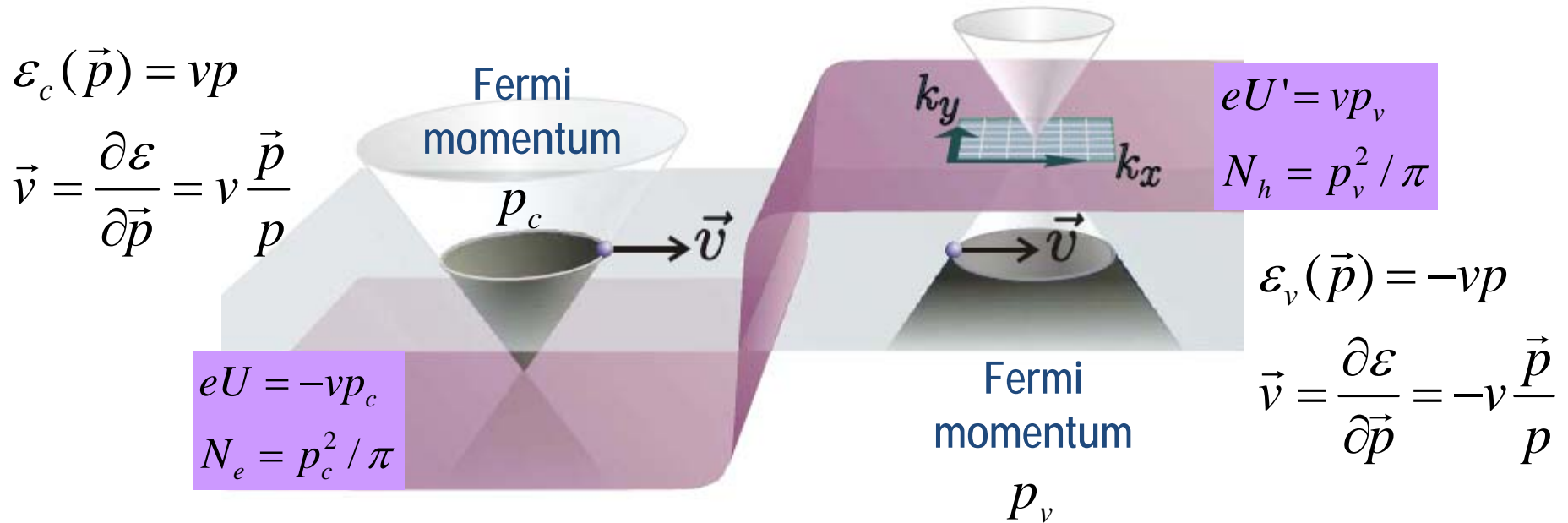
Ballistic graphene:
1 μm mean free path
proven by Fabri-Perot
oscillations of dI/dV



Fabri-Perot oscillations
of critical supercurrent in
S-G-S devices



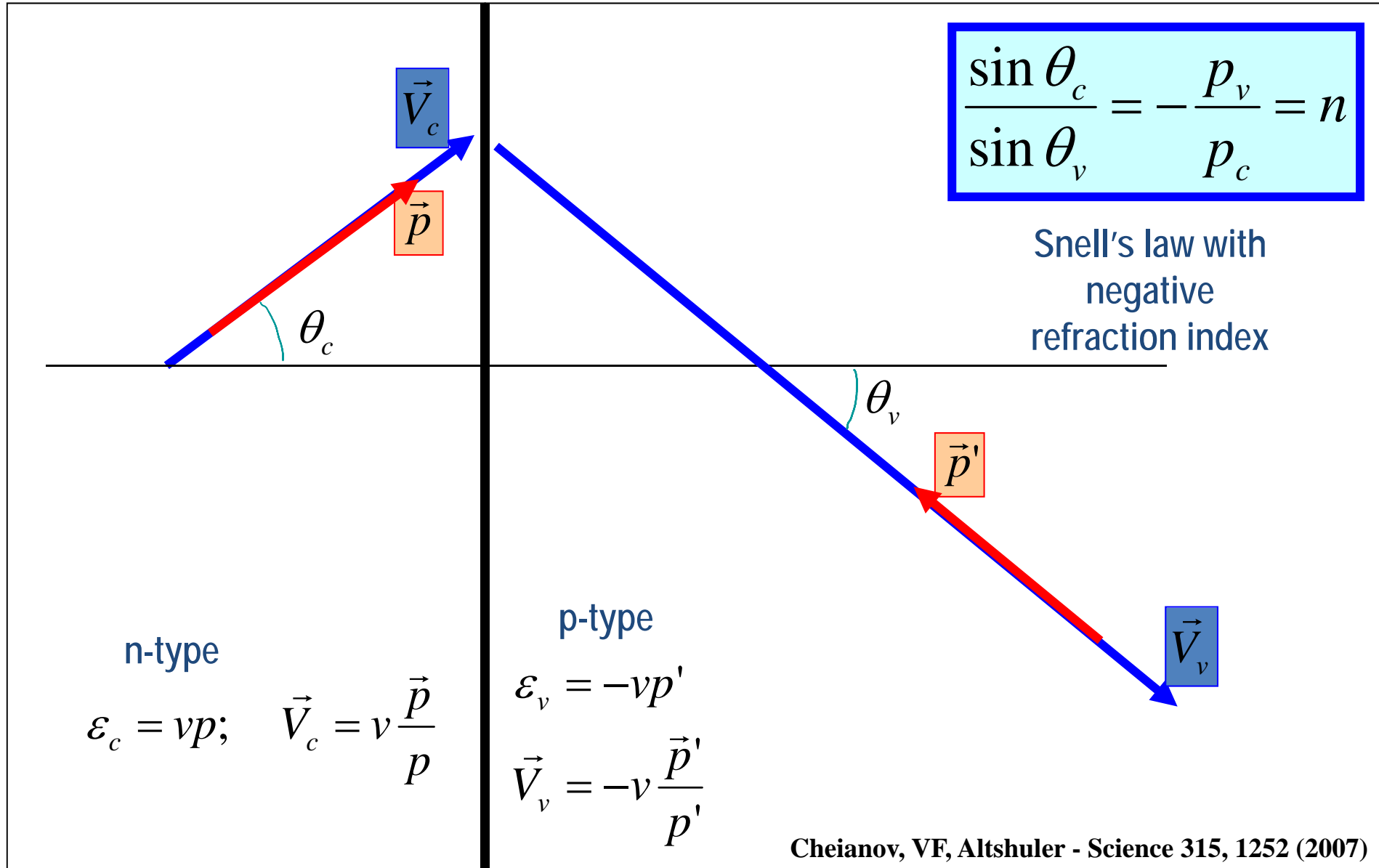
Negative refraction of electrons at p-n interface

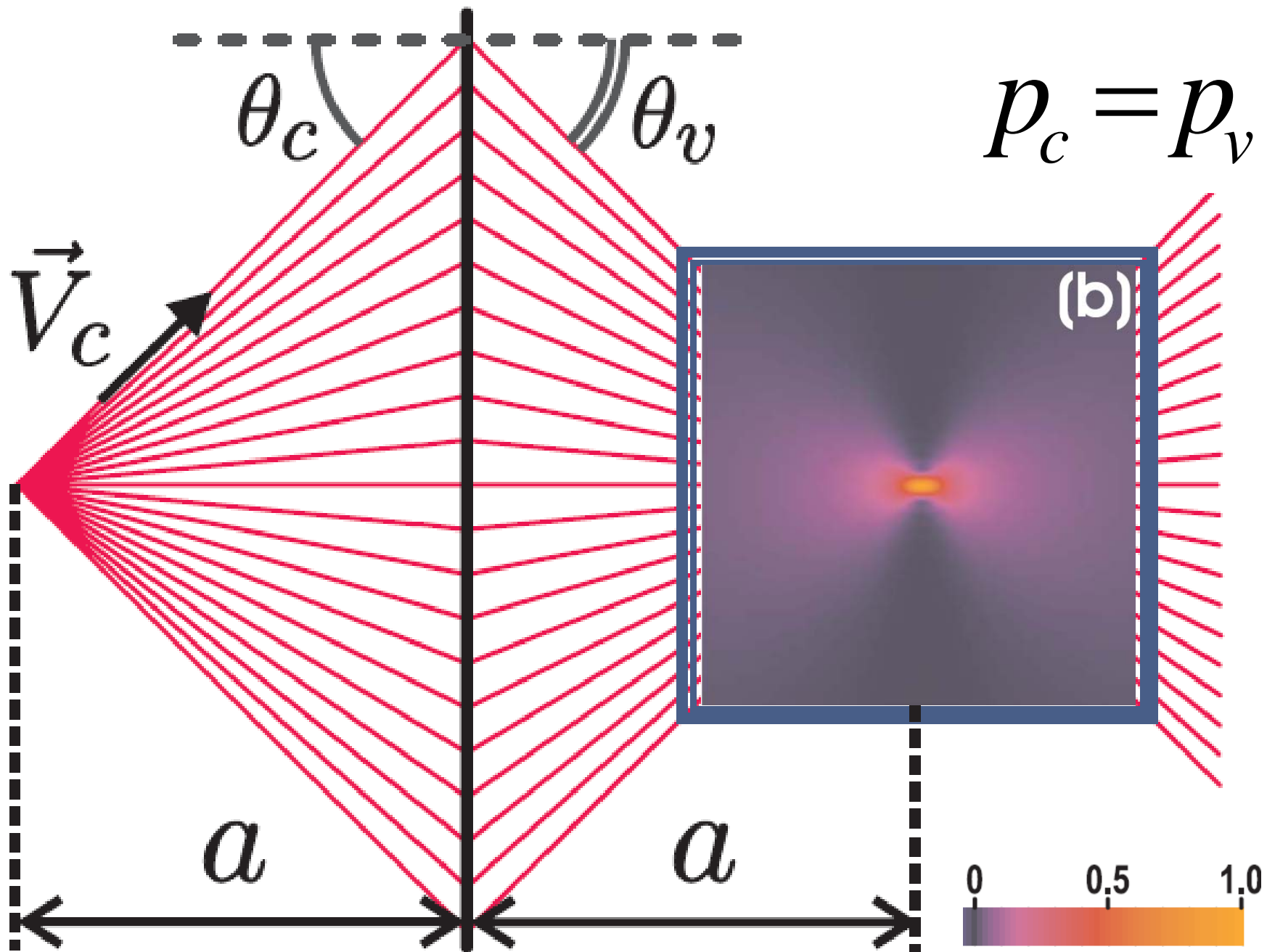


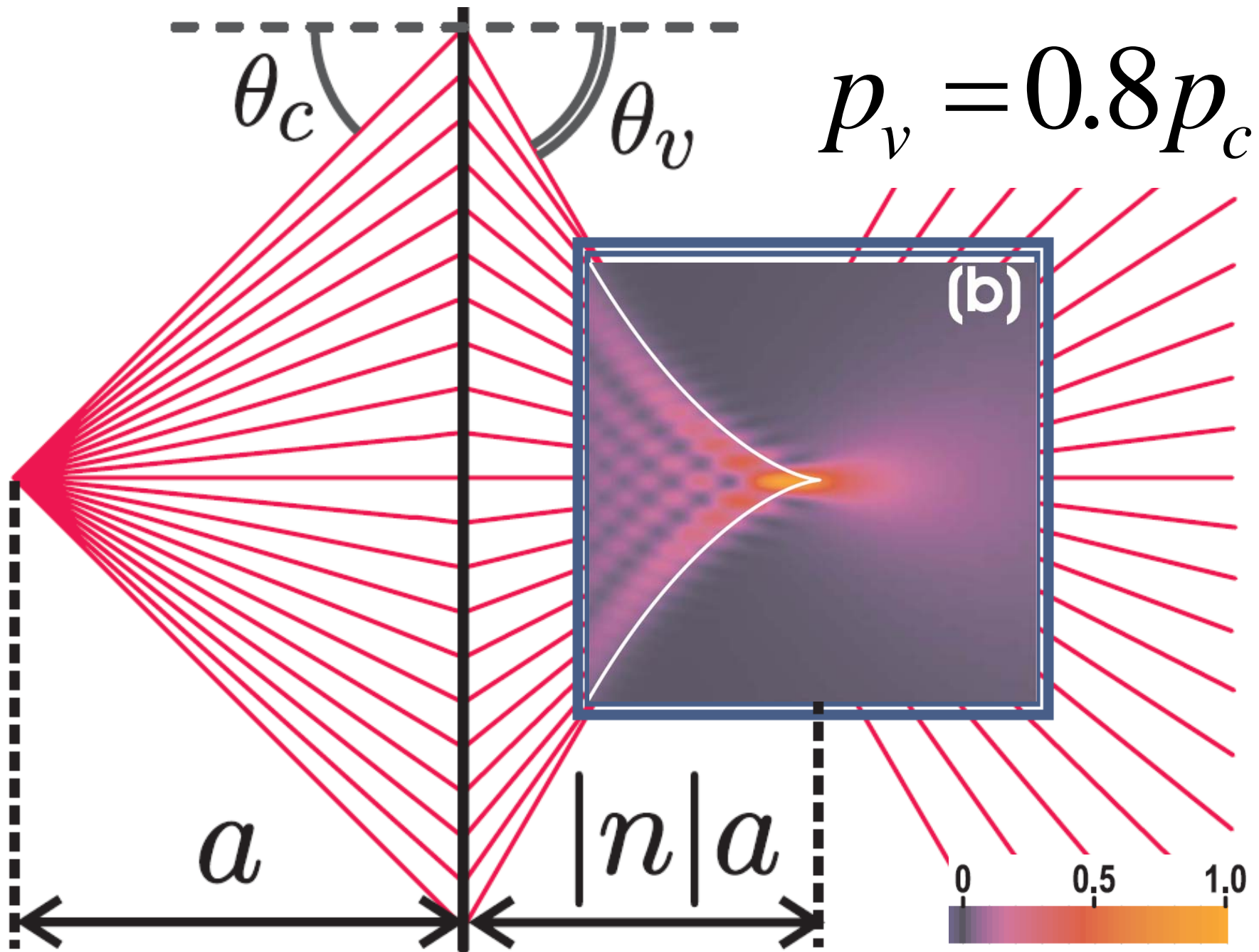
The effect would be the strongest in sharp PN junction, with $d \sim \lambda_F$, which is possible to achieve in hBN-encapsulated graphene.

$$p_y = p'_y \Rightarrow p_c \sin \theta_c = -p_v \sin \theta_v$$

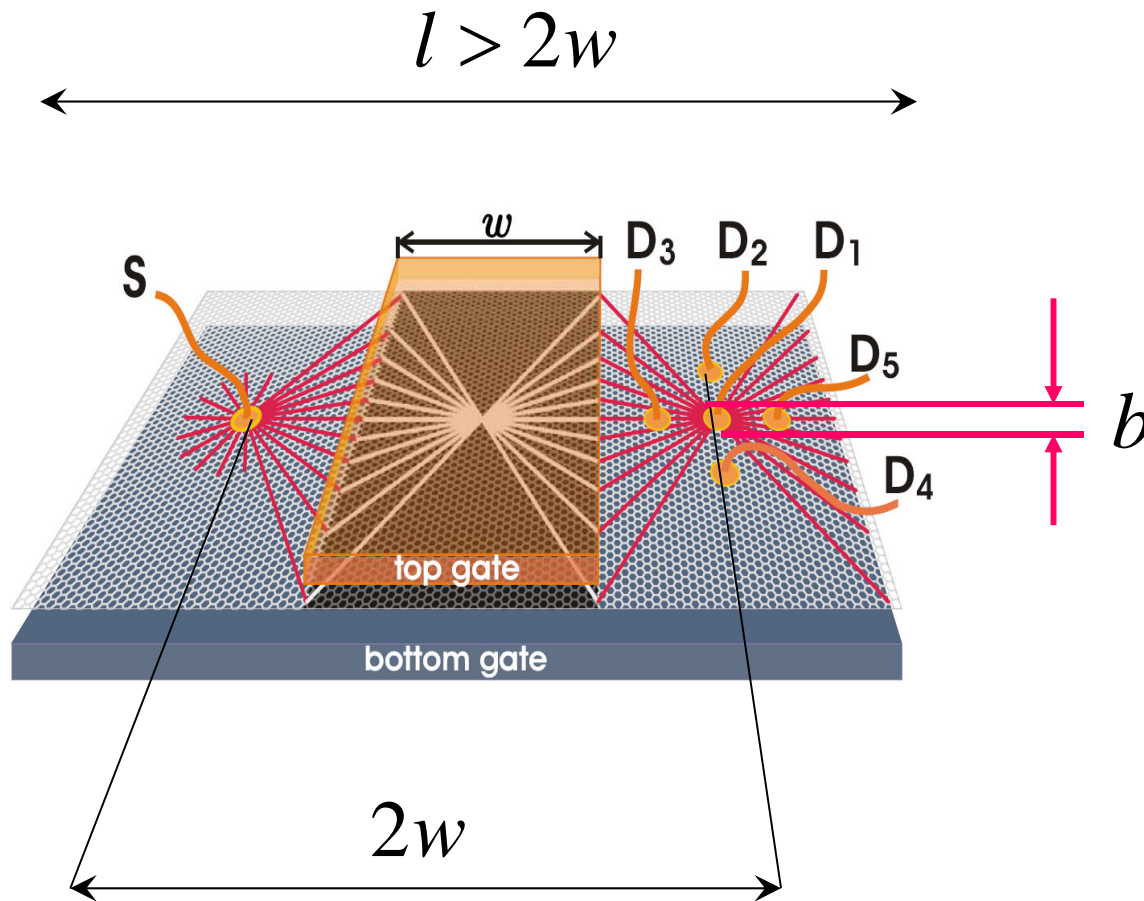
p-n junction







Veselago lens for electrons in ballistic graphene



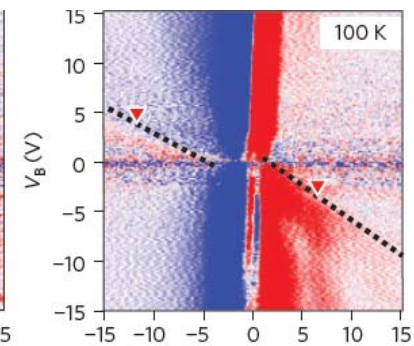
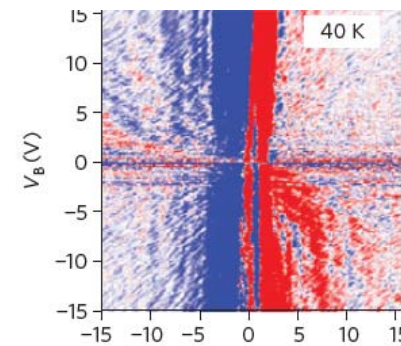
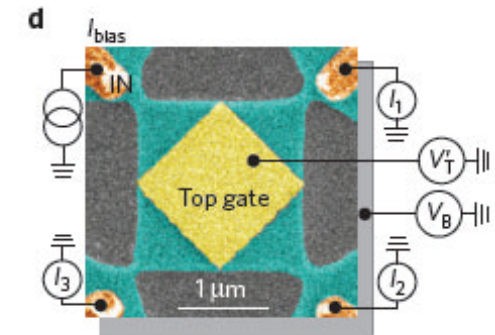
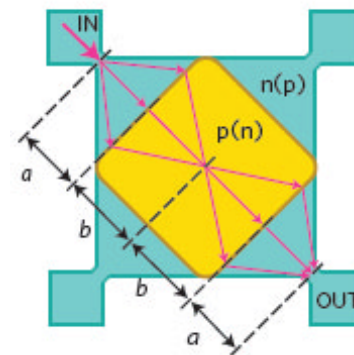
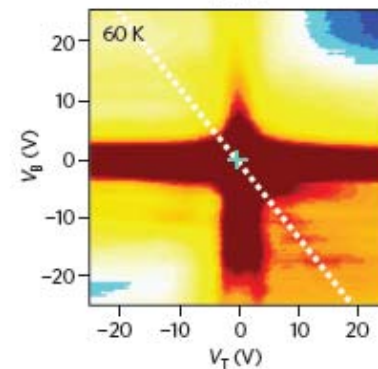
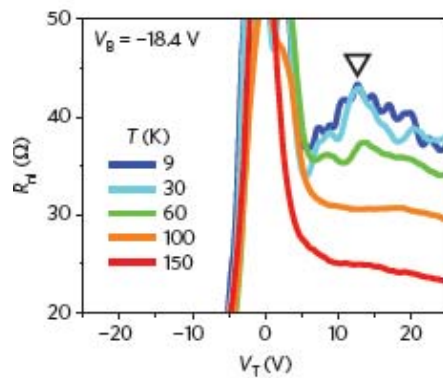
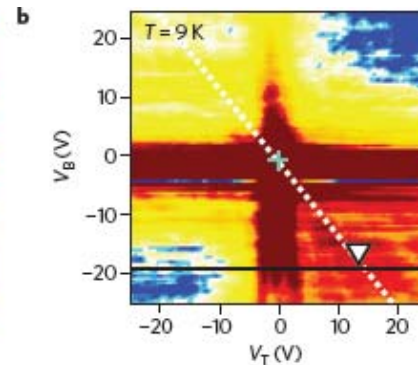
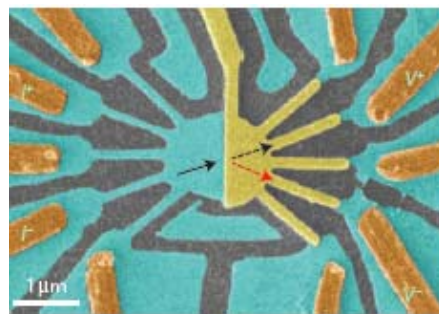
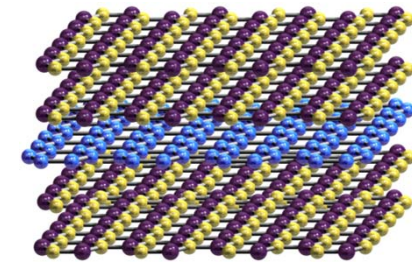
$$kT < \frac{b}{w} \varepsilon_F$$

Cheianov, VF, Altshuler - Science 315, 1252 (2007)

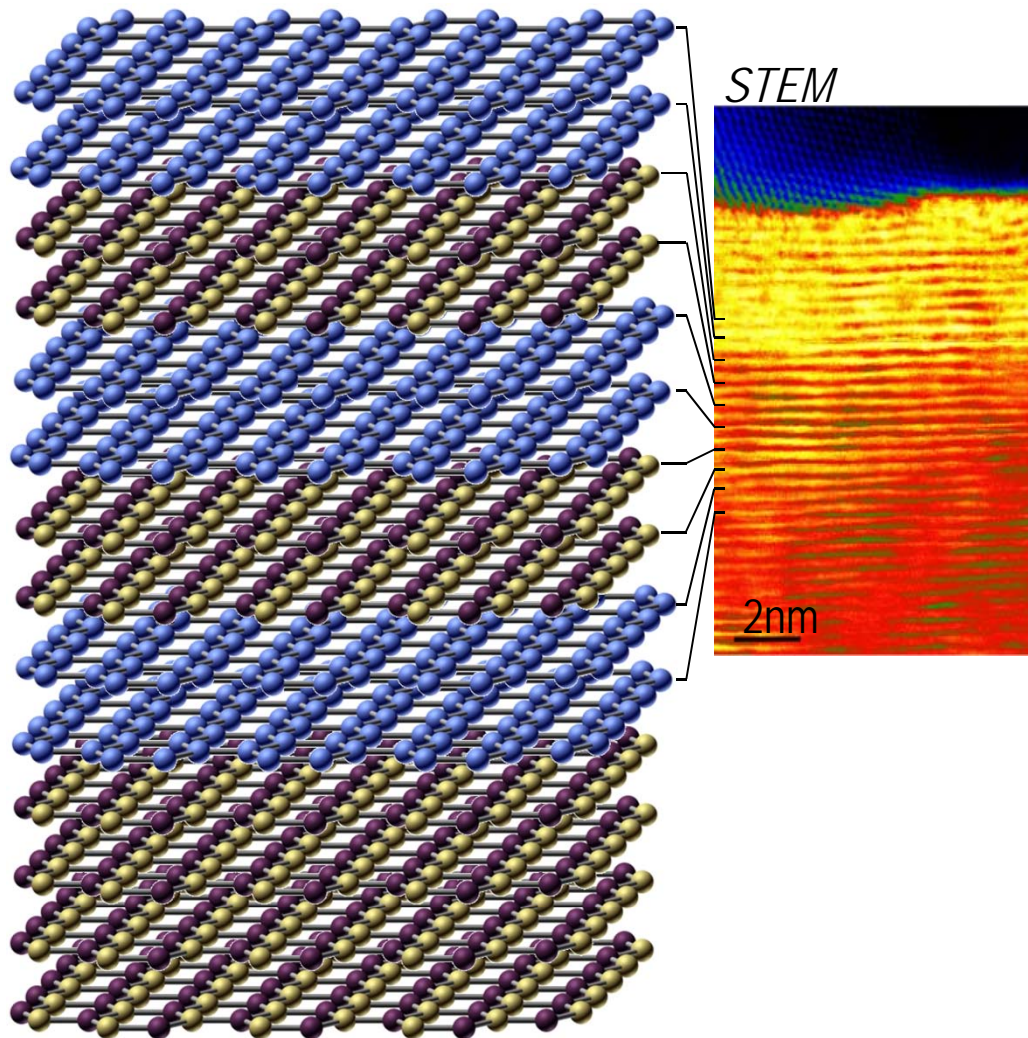
Cheianov, Fal'ko, Altshuler - Science 315, 1252 (2007)

Observation of negative refraction of Dirac fermions in graphene

Gil-Ho Lee[†], Geon-Hyoung Park and Hu-Jong Lee^{*}

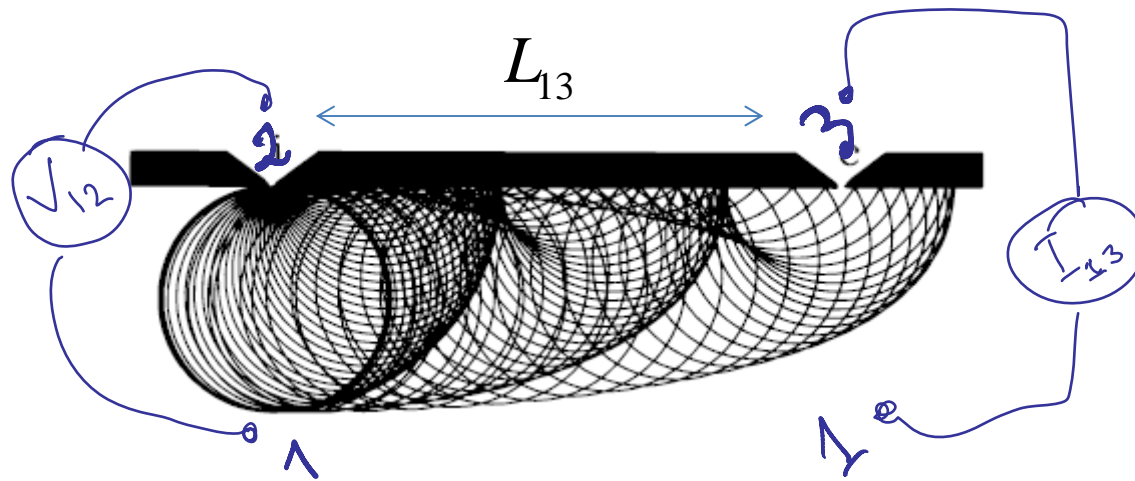


Ballistic G/hBN heterostructures: focusing and caustics in graphene devices

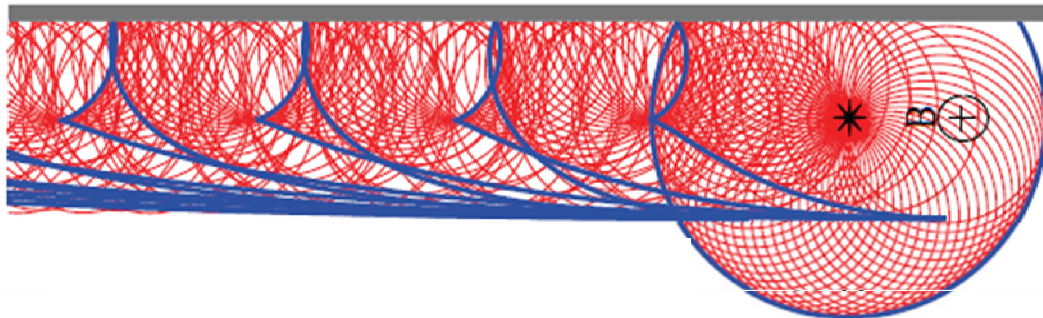


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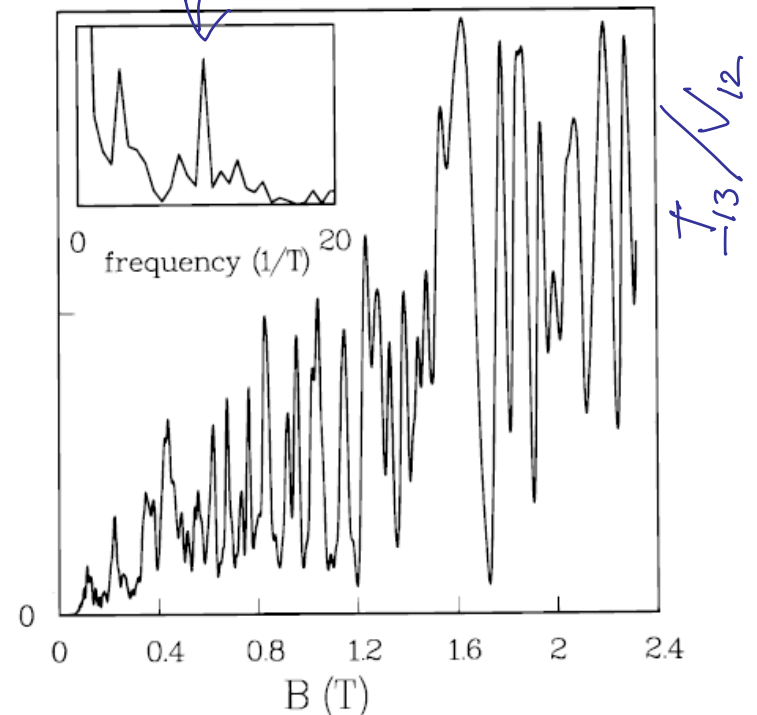
Caustics in the electron skipping motion



$$R_c = \frac{p_F}{eB}$$

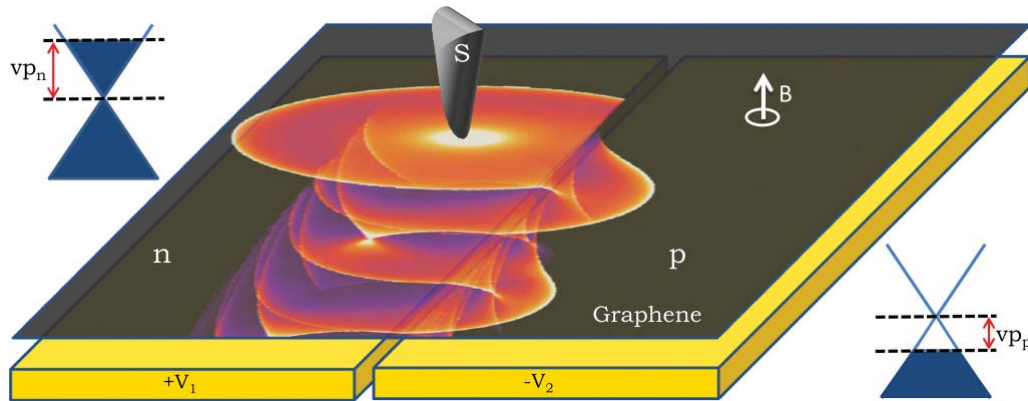


corresponds to $NR_c = L_{13}$

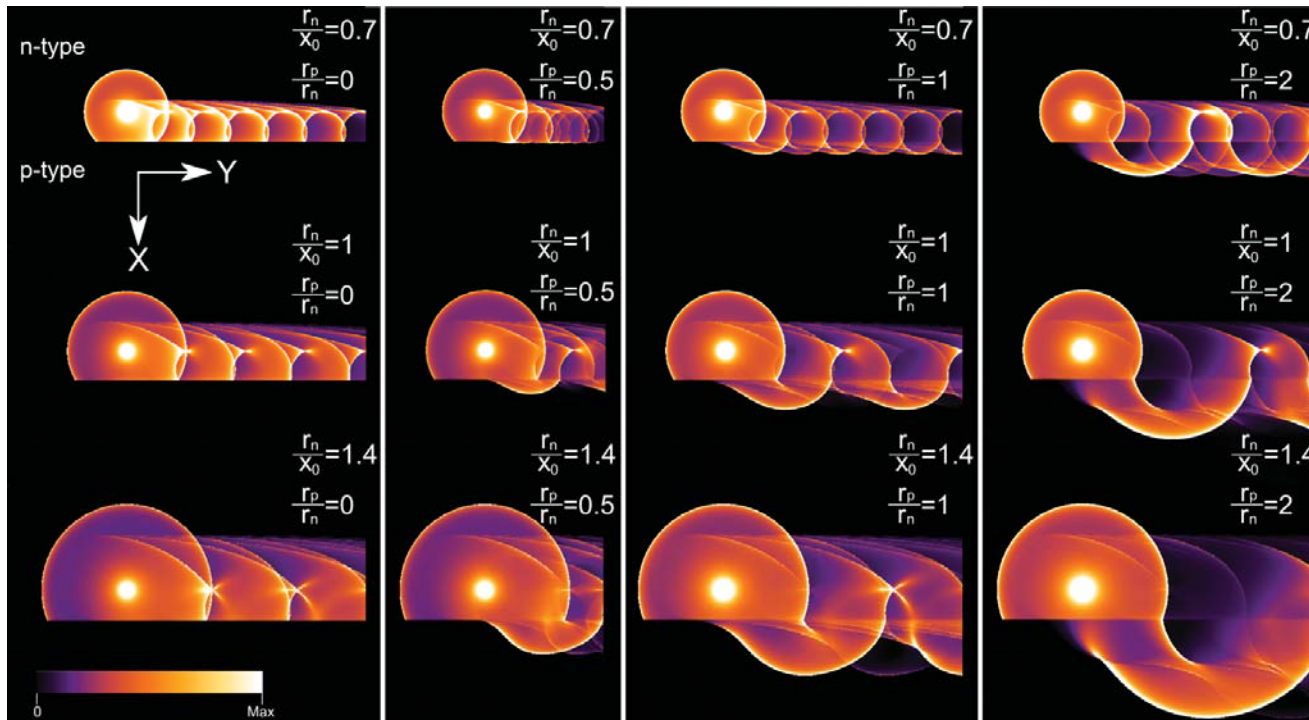


Beenakker, van Houten, van Wees - Europhys. Lett. 7, 359 (1988)
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 Smet, Weiss, Blick, Lutjering, von Klitzing, Fleischmann, Ketzmerick, Geisel, Weimann - Phys. Rev. Lett. 77, 2272 (1996)
 Aidala, Parrott, Kramer, Heller, Westervelt, Hanson, Gossard - Nature Phys. 3, 464 (2007)
 Davies, Patel, Cortijo, Cheianov, Guinea, VF - B 85, 155433 (2012)

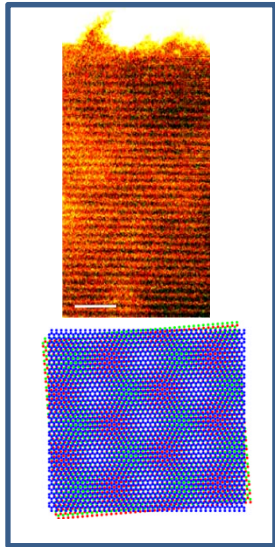
Caustics of electron snake orbits near p-n junction



$$\rho = \int \delta(\mathbf{r} - \mathbf{r}_n) d\varphi d\theta$$

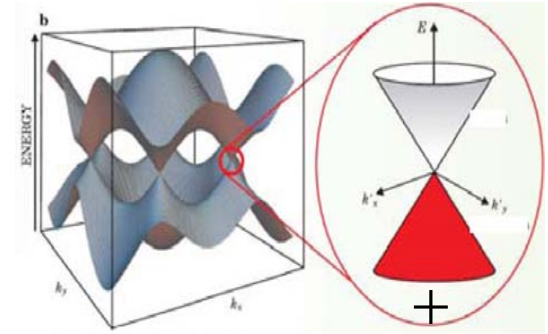


Patel, Davies, Cheianov, VF
Phys Rev B 86, 081413 (2012)



Phenomenological low-energy 'Dirac theory' for electrons in G/hBN moiré superlattices

Wallbank, Patel, Mucha-Kruczynski, Geim, VF - PRB 87, 245408 (2013)

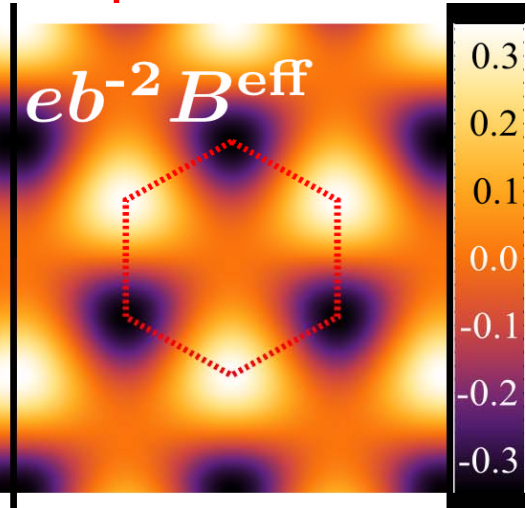
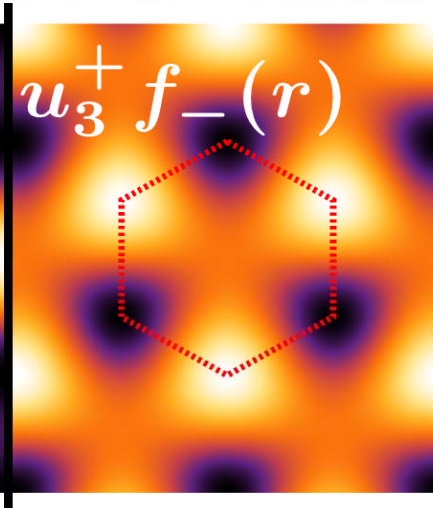
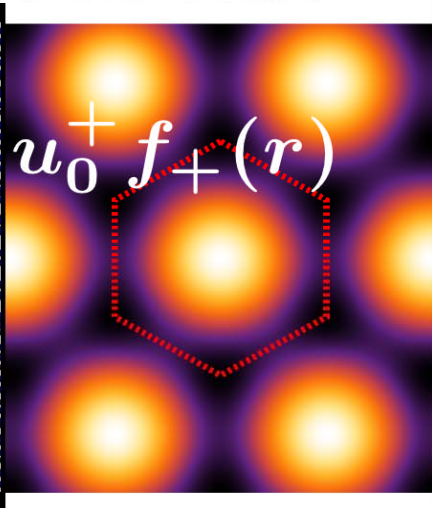
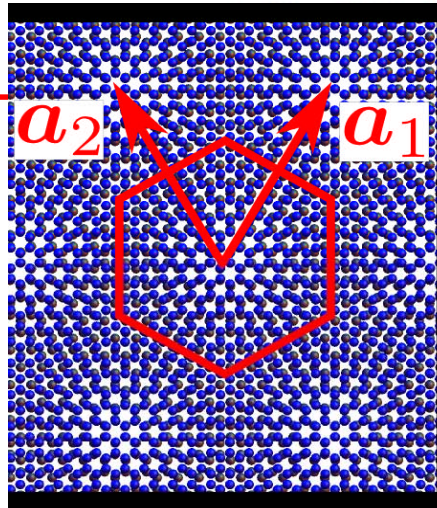


δH_{moire}

graphene sublattice

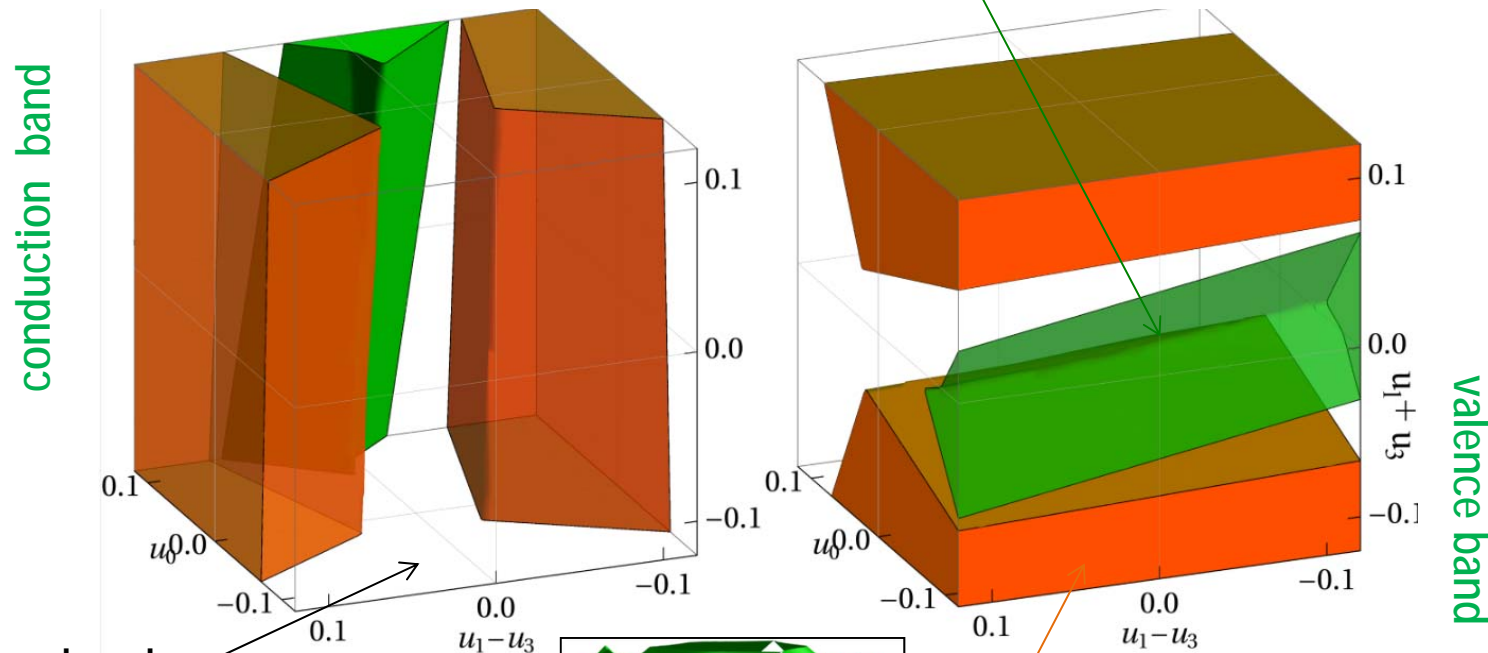
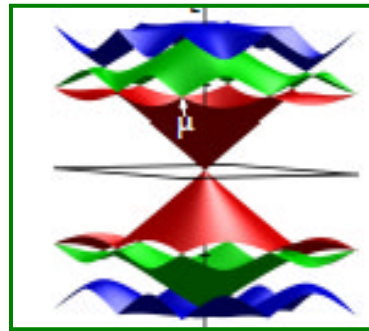
graphene valley

$$\hat{H} = vp \cdot \sigma + u_0 v b f_1(r) + u_3 v b f_2(r) \sigma_3 \tau_3 + u_1 v [l_z \times \nabla f_2(r)] \cdot \sigma \tau_3 \quad \text{inversion symmetric}$$



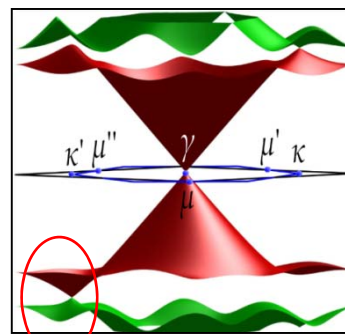
characteristic
moiré miniband
regimes

Three mini-DPs at the
edge of 1st miniband



Overlapping bands
hiding mini-DPs of
moiré minibands

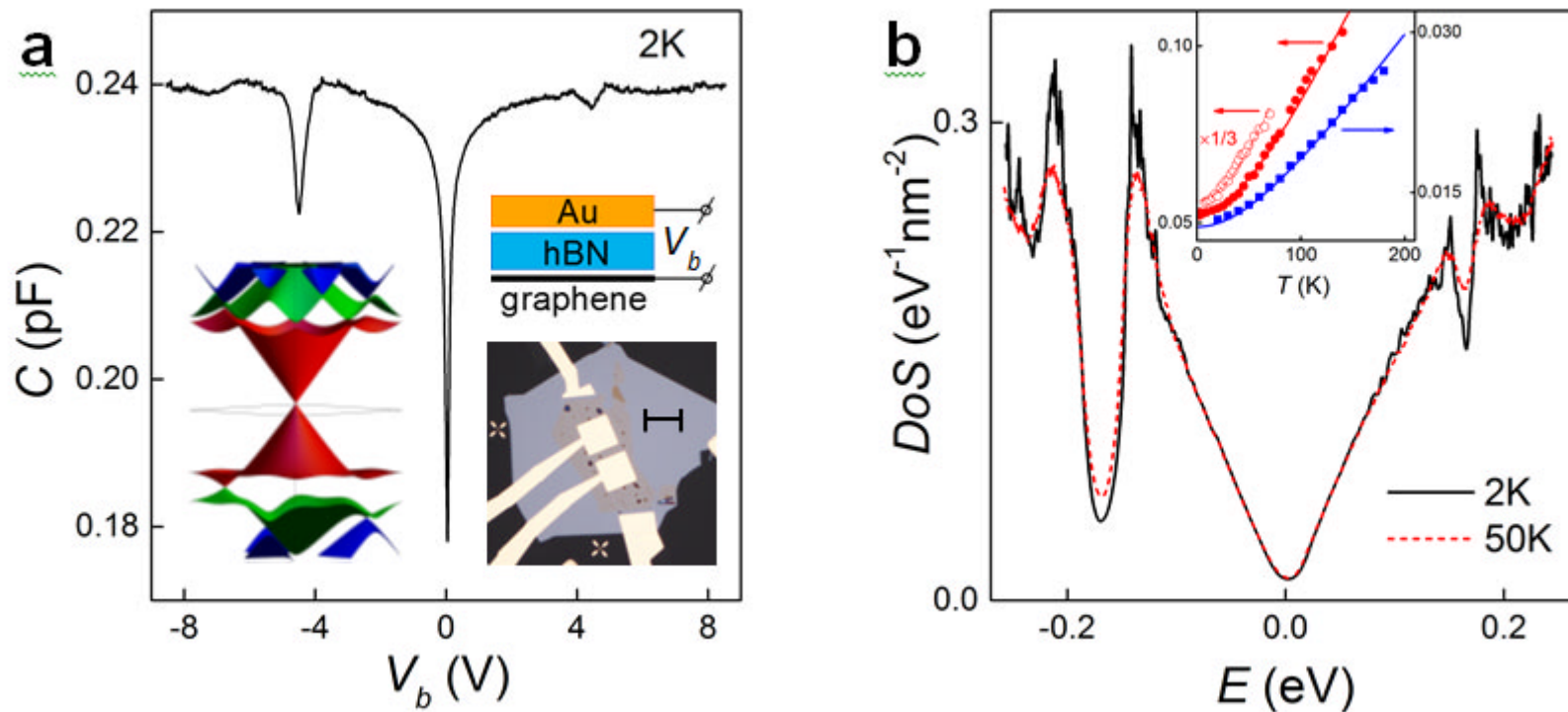
vb



single mini-DP at the
edge of 1st miniband

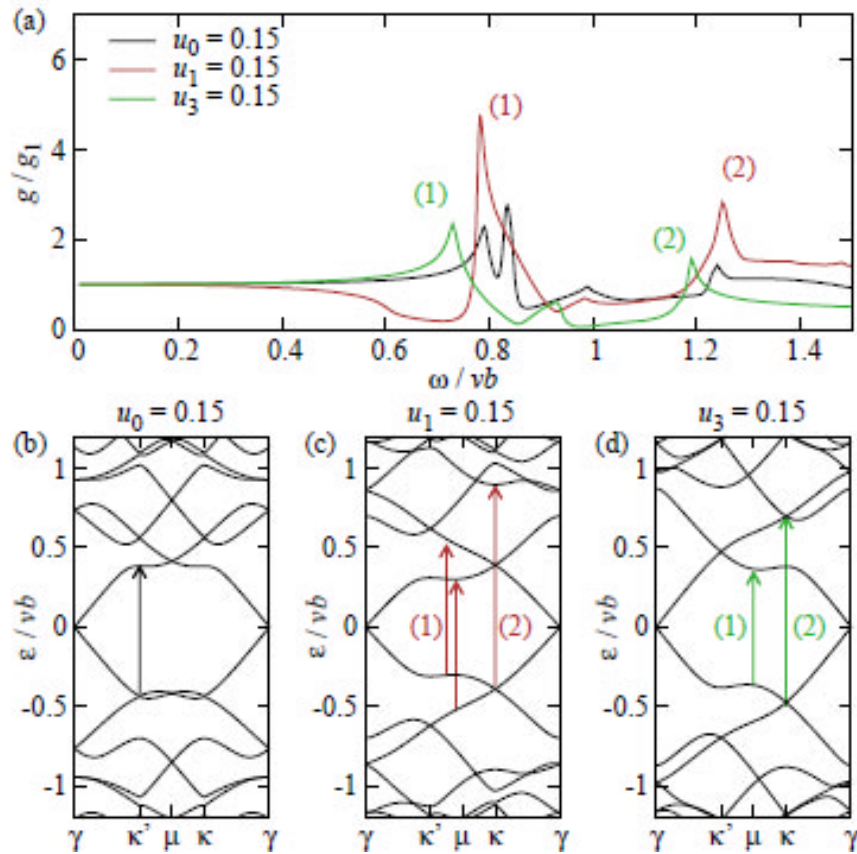
$$v_{mDP} \approx \frac{1}{2} v$$

Capacitance spectroscopy of moiré minibands in G-hBN heterostructures

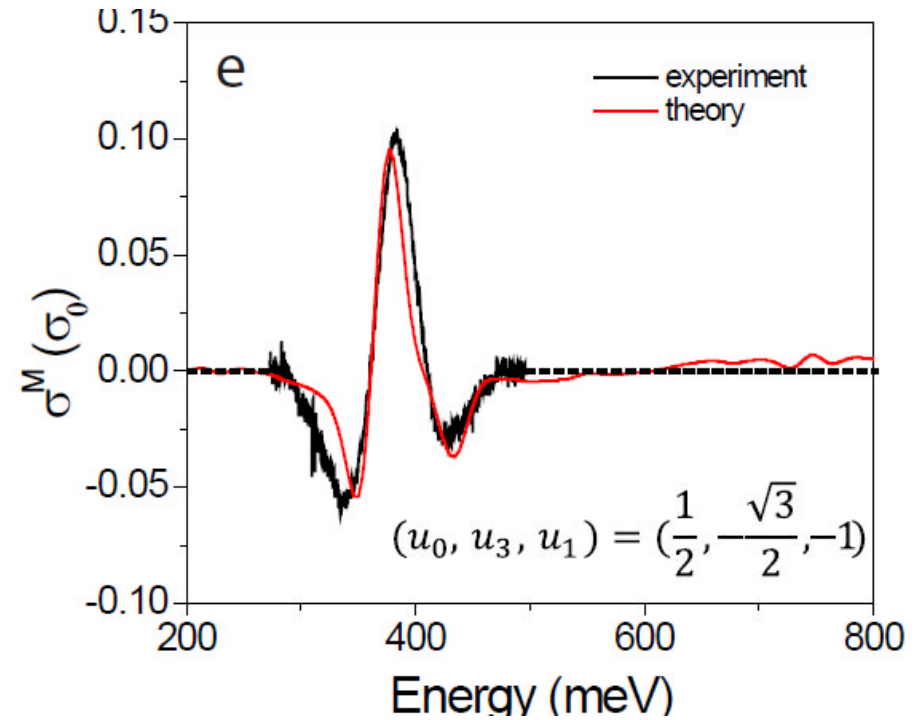


Yu, Gorbachev, Tu, Kretinin, Cao, Jalil, Withers, Ponomarenko, Chen, Piot, Potemski, Elias, Watanabe, Taniguchi, Grigorieva, Novoselov, VF, Geim, Mishchenko - Nature Physics 10, 525 (2014)

Optical signature of moiré minibands

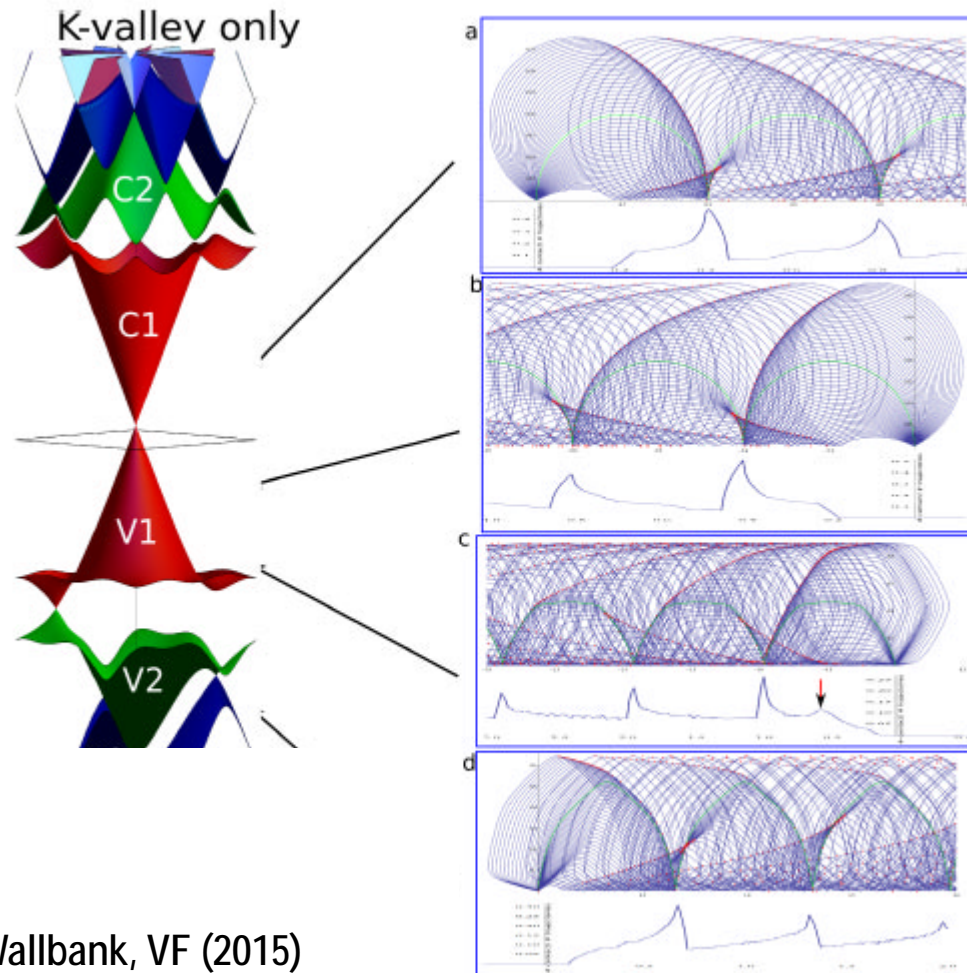


Abergel, Wallbank, Chen, Mucha-Kruczynski, VF
New J Phys 15, 123009 (2013)

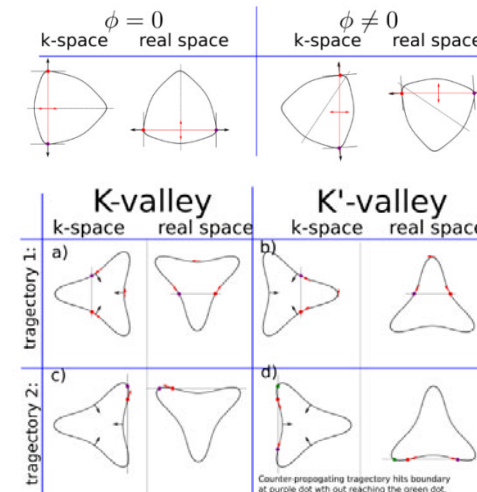


Shi, Jin, Yang, Ju, Horng, Lu, Bechtel, Martin, Fu, Wu,
Watanabe, Taniguchi, Zhang, Bai, Wang, Zhang, Wang
arXiv:1405.2032

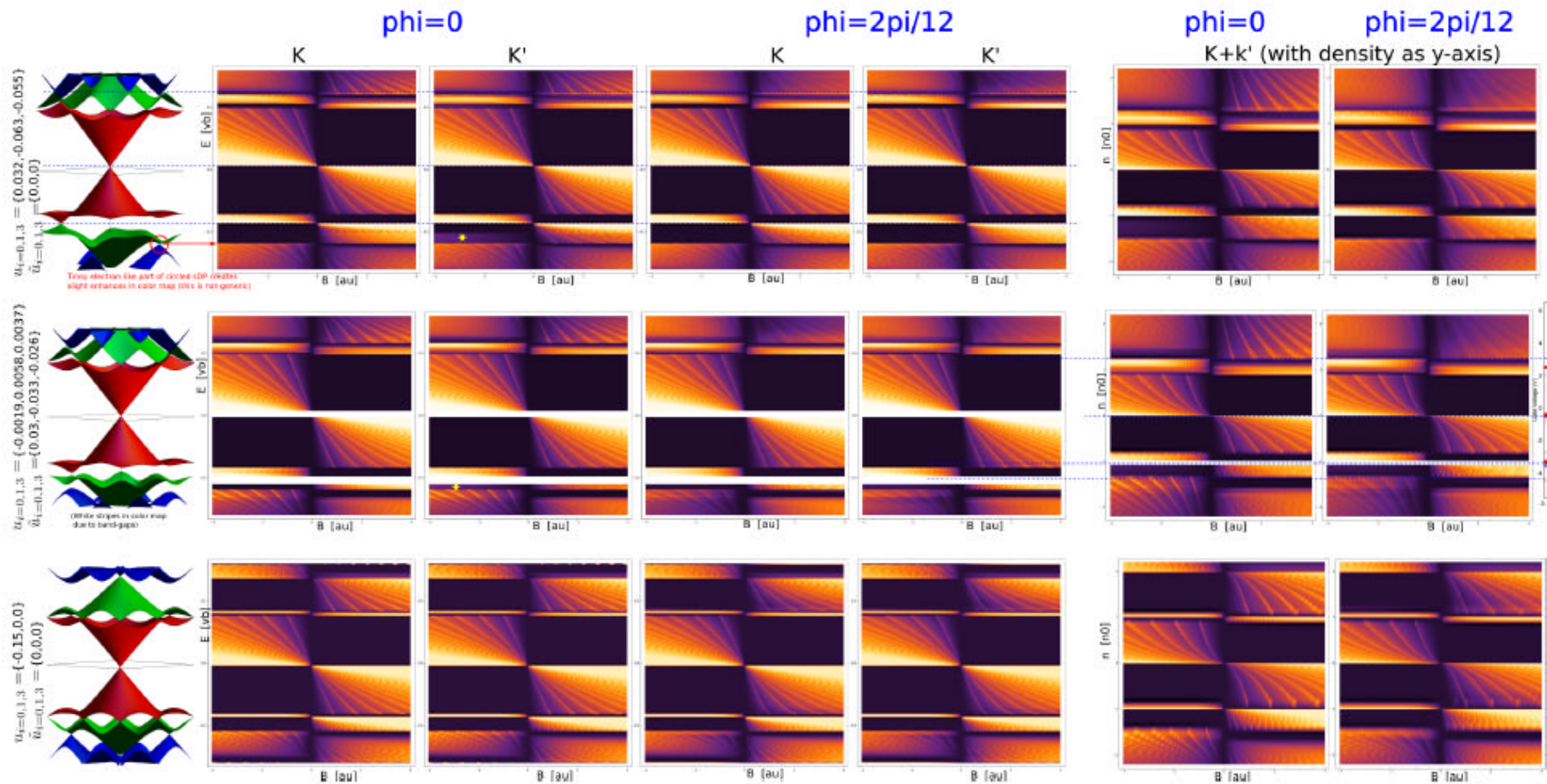
Focusing of electrons in moiré minibands in G-hBN heterostructures



Wallbank, VF (2015)



Focusing of electrons in moiré minibands in G-hBN heterostructures



Ballistic G/hBN heterostructures: focusing and caustics in graphene devices

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in collaboration with

John Wallbank (NGI Manchester)

Aavishkar Patel (Harvard), Nathan Davis (BAE), Paco Guinea (Madrid)

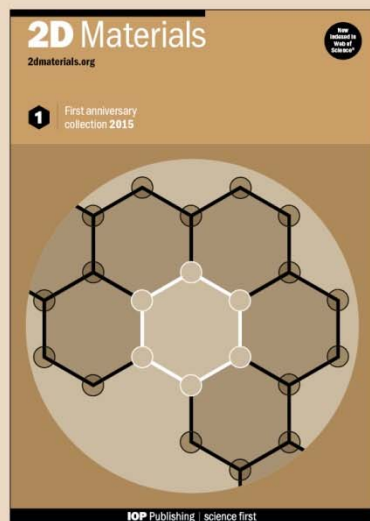
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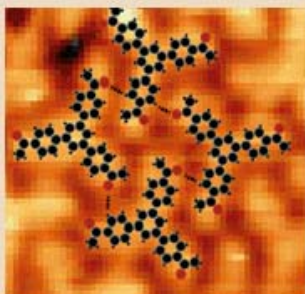
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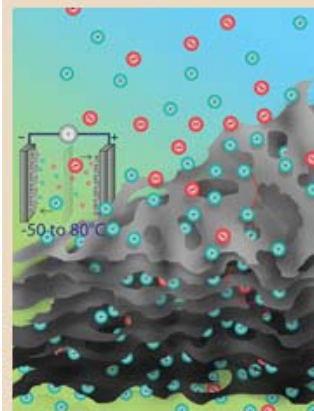
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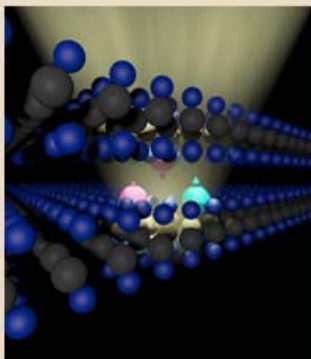
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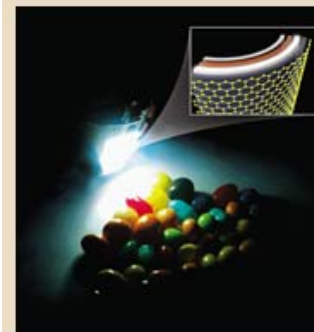
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